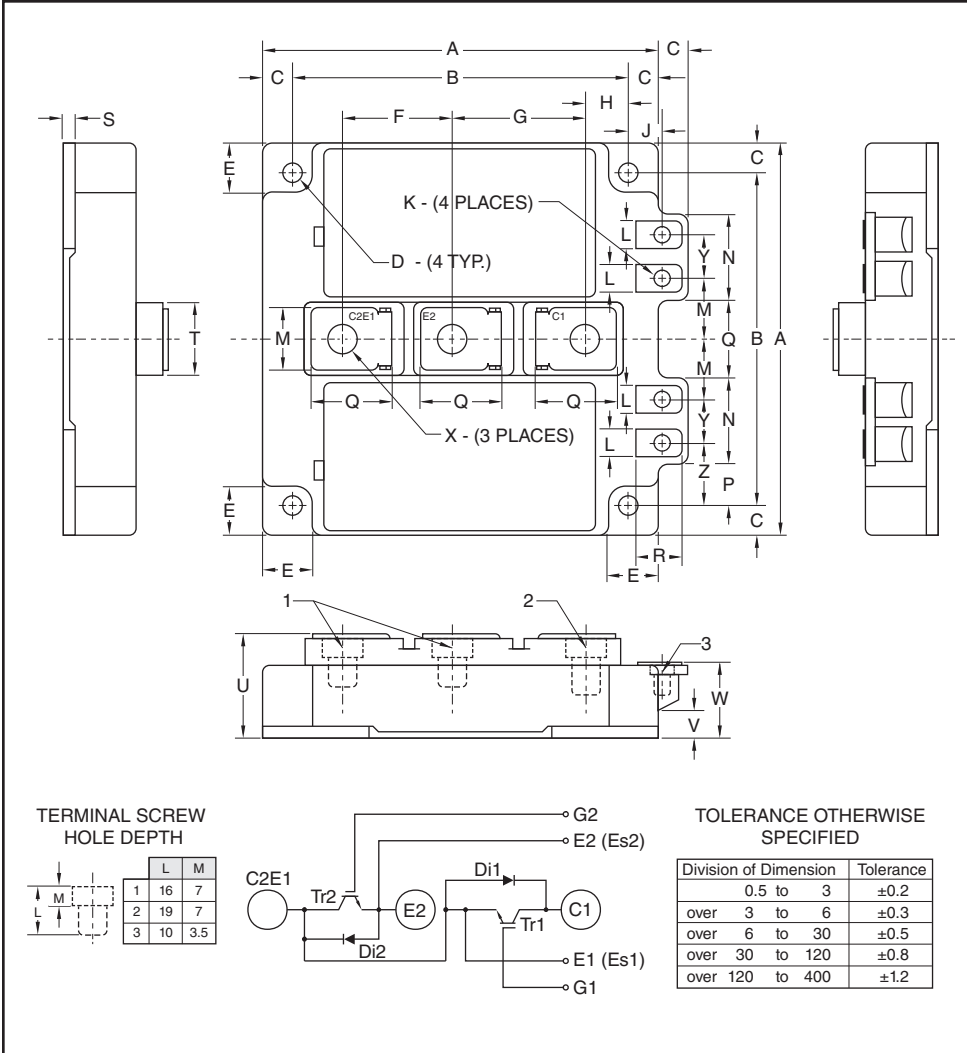


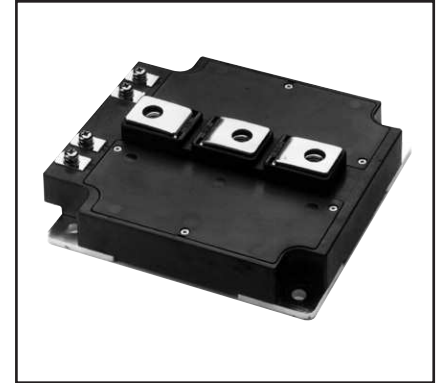
Dual IGBT A-Series Module 400 Amperes/1700 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.12	130.0
B	4.33±0.008	110.0±0.2
C	0.39	10.0
D	0.26 Dia.	6.5 Dia.
E	0.65	16.5
F	1.42	36.0
G	1.72	43.8
H	0.54	13.8
J	0.45	11.5
K	M4	M4
L	0.35	9.0
M	0.78	20.0

Dimensions	Inches	Millimeters
N	1.12	28.5
P	0.53	13.5
Q	1.02	26.0
R	0.59	15.0
S	0.16	4.0
T	0.95	24.0
U	1.38+0.04/-0.02	35.0+1.0/-0.5
V	0.35	9.1
W	0.97+0.04/-0.02	24.5+1.0/-0.5
X	M8	M8
Y	0.57	14.5
Z	0.80	20.5



Description:

Powerex IGBT Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- UPS
- Battery Powered Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM400DY-34A is a 1700V (V_{CES}), 400 Ampere Dual IGBT Power Module.

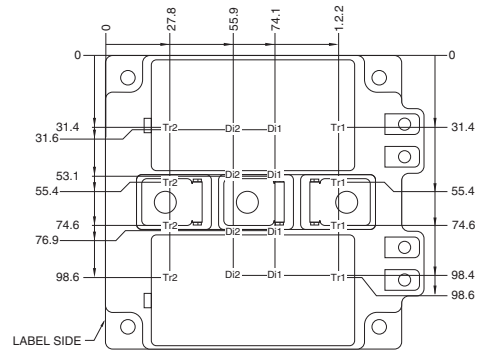
Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	400	34

CM400DY-34A
Dual IGBT A-Series Module
 400 Amperes/1700 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Rating	Units
Collector-Emitter Voltage (G-E Short-Circuited)	V_{CES}	1700	Volts
Gate-Emitter Voltage (C-E Short-Circuited)	V_{GES}	± 20	Volts
Collector Current (DC, $T_C = 107^\circ\text{C}$)*2,*4	I_C	400	Amperes
Collector Current (Pulse, Repetitive)*3	I_{CRM}	800	Amperes
Total Power Dissipation ($T_C = 25^\circ\text{C}$)*2,*4	P_{tot}	3780	Watts
Emitter Current ($T_C = 25^\circ\text{C}$)*2,*4	I_E^{*1}	400	Amperes
Emitter Current (Pulse, Repetitive)*3	I_{ERM}^{*1}	800	Amperes
Junction Temperature	T_j	-40 ~ +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 ~ +125	$^\circ\text{C}$
Isolation Voltage (Terminals to Baseplate, RMS, $f = 60\text{Hz}$, AC 1 minute)	V_{iso}	3500	Volts

- *1 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDi).
- *2 Case temperature (T_C) and heatsink temperature (T_S) is measured on the surface (mounting side) of the baseplate and the heatsink side just under the chips. Refer to the figure to the right for chip location. The heatsink thermal resistance should be measured just under the chips.
- *3 Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.
- *4 Junction temperature (T_j) should not increase beyond maximum junction temperature ($T_{j(max)}$) rating.



Tr1 / Tr2: IGBT, Di1 / Di2: FWDi

CM400DY-34A
Dual IGBT A-Series Module
 400 Amperes/1700 Volts

Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Emitter Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, G-E Short-Circuited	—	—	1.0	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = V_{GES}$, C-E Short-Circuited	—	—	2.0	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 40\text{mA}$, $V_{CE} = 10\text{V}$	5.5	7.0	8.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 400\text{A}$, $V_{GE} = 15\text{V}$, $T_j = 25^\circ\text{C}^{*5}$	—	2.2	2.8	Volts
		$I_C = 400\text{A}$, $V_{GE} = 15\text{V}$, $T_j = 125^\circ\text{C}^{*5}$	—	2.45	—	Volts
Input Capacitance	C_{ies}		—	—	98.8	nF
Output Capacitance	C_{oes}	$V_{CE} = 10\text{V}$, G-E Short-Circuited	—	—	11.2	nF
Reverse Transfer Capacitance	C_{res}		—	—	2.1	nF
Gate Charge	Q_G	$V_{CC} = 1000\text{V}$, $I_C = 400\text{A}$, $V_{GE} = 15\text{V}$	—	2670	—	nC
Turn-on Delay Time	$t_{d(on)}$		—	—	950	ns
Rise Time	t_r	$V_{CC} = 1000\text{V}$, $I_C = 400\text{A}$, $V_{GE} = \pm 15\text{V}$,	—	—	300	ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 1.2\Omega$, Inductive Load	—	—	1000	ns
Fall Time	t_f		—	—	350	ns
Emitter-Collector Voltage	V_{EC}^{*1}	$I_E = 400\text{A}$, G-E Short-Circuited ^{*5}	—	2.3	3.0	Volts
Reverse Recovery Time	t_{rr}^{*1}	$V_{CC} = 1000\text{V}$, $I_E = 400\text{A}$, $V_{GE} = \pm 15\text{V}$	—	—	450	ns
Reverse Recovery Charge	Q_{rr}^{*1}	$R_G = 1.2\Omega$, Inductive Load	—	40	—	μC
Turn-on Switching Energy per Pulse	E_{on}	$V_{CC} = 1000\text{V}$, $I_C = I_E = 400\text{A}$,	—	197.3	—	mJ
Turn-off Switching Energy per Pulse	E_{off}	$V_{GE} = \pm 15\text{V}$, $R_G = 1.2\Omega$,	—	117.9	—	mJ
Reverse Recovery Energy per Pulse	E_{rr}^{*1}	$T_j = 125^\circ\text{C}$, Inductive Load	—	98.5	—	mJ
Internal Gate Resistance	r_g	Per Switch, $T_C = 25^\circ\text{C}$	—	3.7	—	Ω

*1 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDi).

*5 Pulse width and repetition rate should be such as to cause negligible temperature rise.

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Thermal Resistance Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case* ²	$R_{th(j-c)Q}$	Per IGBT	—	—	33	K/kW
Thermal Resistance, Junction to Case* ²	$R_{th(j-c)D}$	Per IFWDi	—	—	55	K/kW
Contact Thermal Resistance, Case to Heatsink	$R_{th(c-s)}$	Thermal Grease Applied* ⁶ (Per 1/2 Module)	—	19	—	K/kW

Mechanical Characteristics

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Mounting Torque	M_t	Main Terminals, M8 Screw	78	85	95	in-lb
		Auxiliary (G, E) Terminals, M4 Screw	11	13	15	in-lb
		M_s	Mounting to Heatsink, M6 Screw	31	35	40
Weight	m		—	1200	—	Grams
Flatness of Baseplate	e_c	On Centerline X, Y* ⁷	-100	—	+100	μm

Recommended Operating Conditions, $T_a = 25^\circ\text{C}$

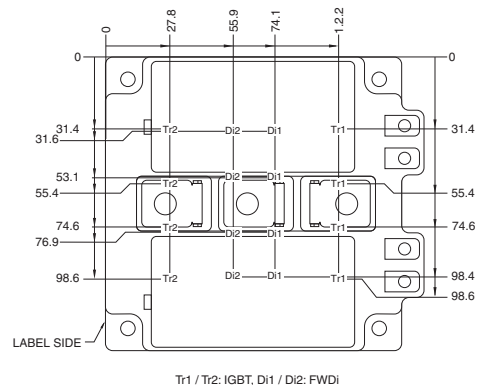
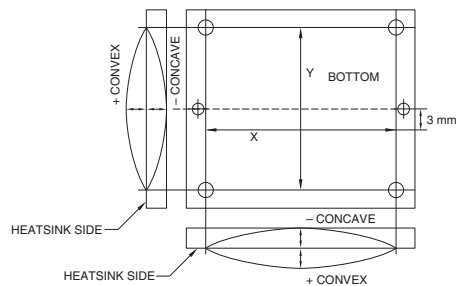
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
(DC) Supply Voltage	V_{CC}	Applied Across C1-E2	—	1000	1150	Volts
Gate (-Emitter Drive) Voltage	$V_{GE(on)}$	Applied Across G1-Es1 / G2-Es2	13.5	15.0	16.5	Volts
External Gate Resistance	R_G	Per Switch	1.2	—	12	Ω

*² Case temperature (T_C) and heatsink temperature (T_S) is measured on the surface (mounting side) of the baseplate and the heatsink side just under the chips. Refer to the figure to the right for chip location.

The heatsink thermal resistance should be measured just under the chips.

*⁶ Typical value is measured by using thermally conductive grease of $\lambda = 0.9 \text{ [W/(m} \cdot \text{K)]}$.

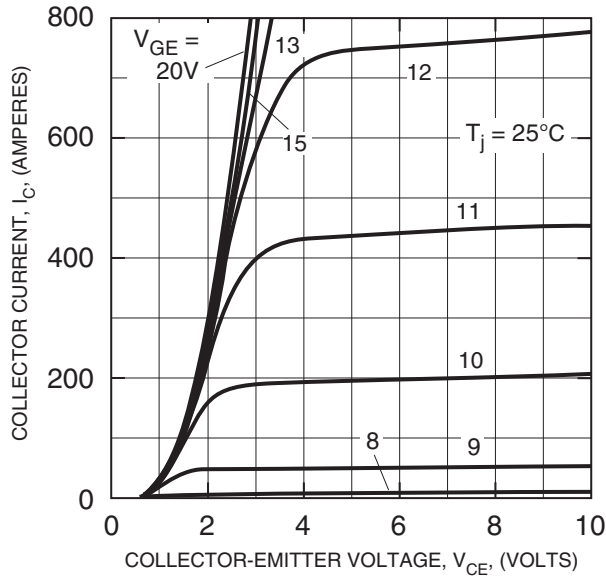
*⁷ Baseplate (mounting side) flatness measurement points (X, Y) are shown in the figure below.



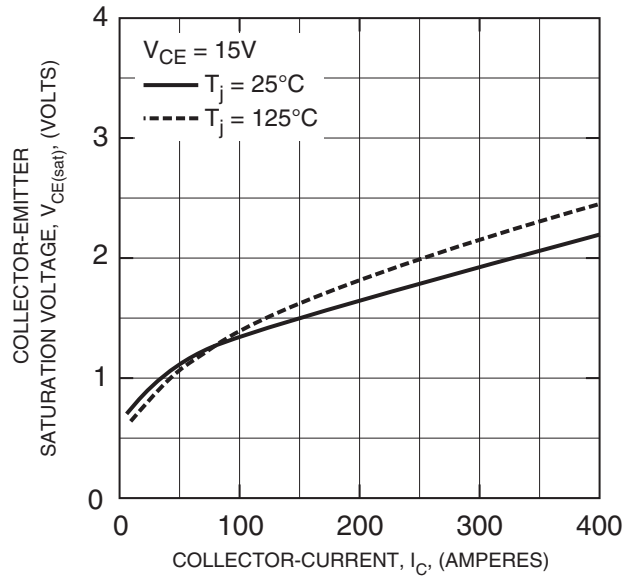
Tr1 / Tr2: IGBT, Di1 / Di2: FWDi

CM400DY-34A
Dual IGBT A-Series Module
 400 Amperes/1700 Volts

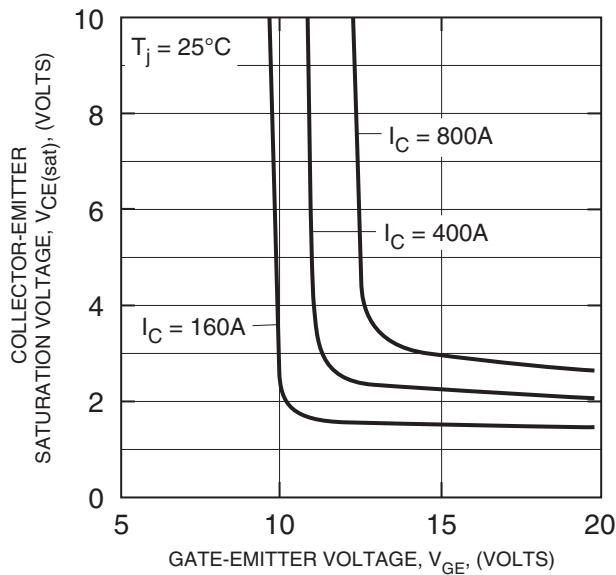
OUTPUT CHARACTERISTICS (TYPICAL)



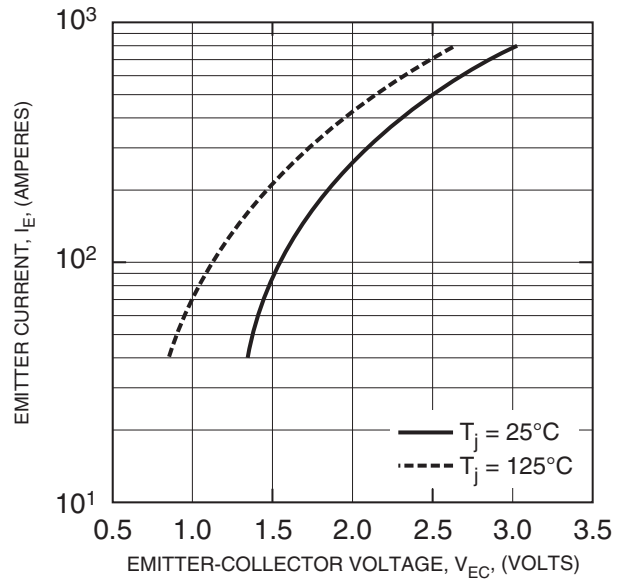
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

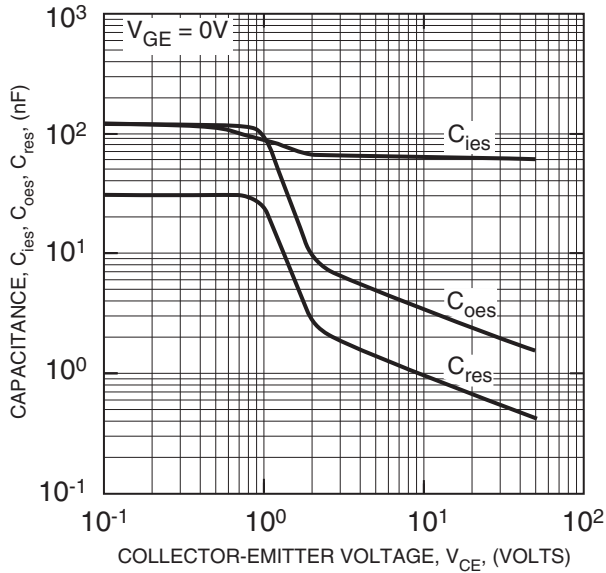


FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)

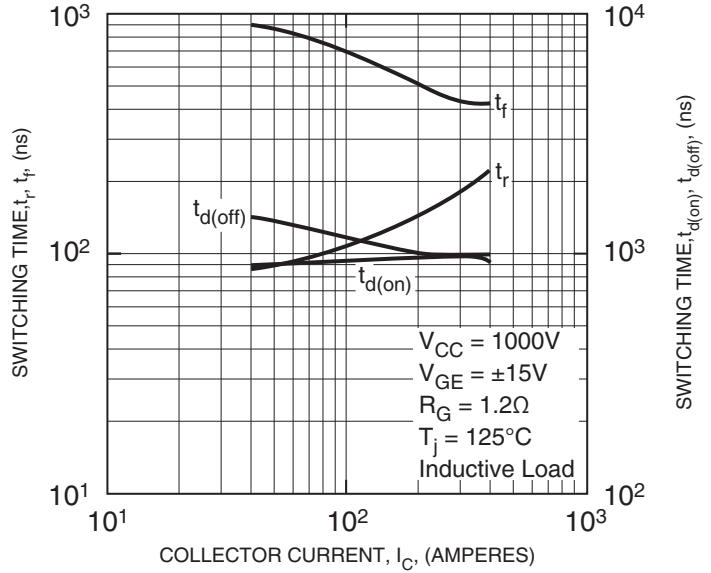


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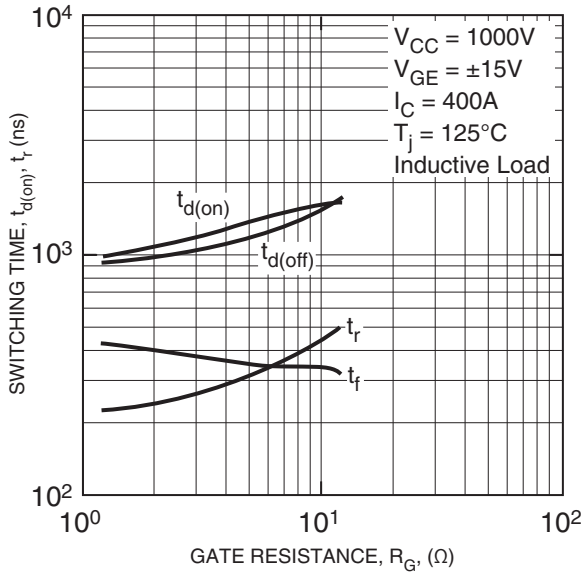
CAPACITANCE VS. V_{CE}
(TYPICAL)



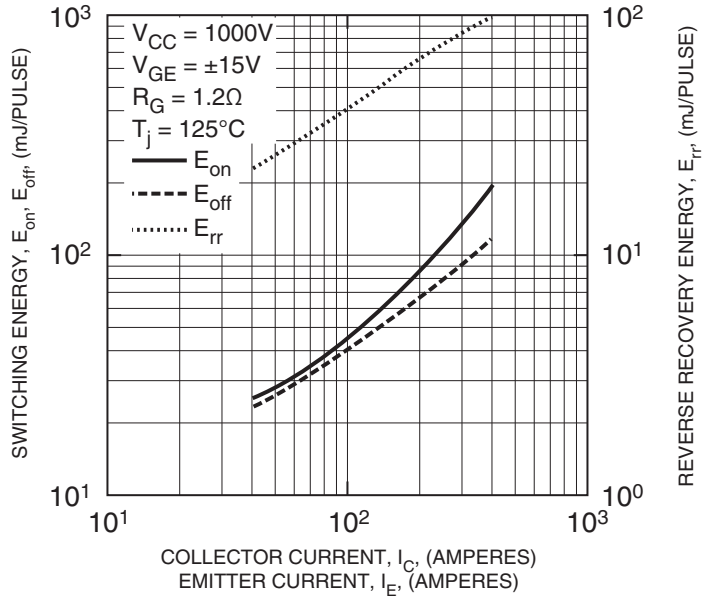
HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)



SWITCHING TIME VS. GATE RESISTANCE
(TYPICAL)

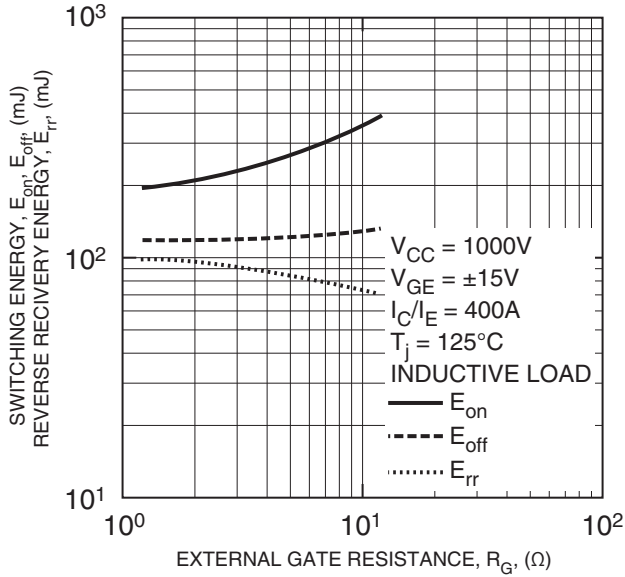


HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

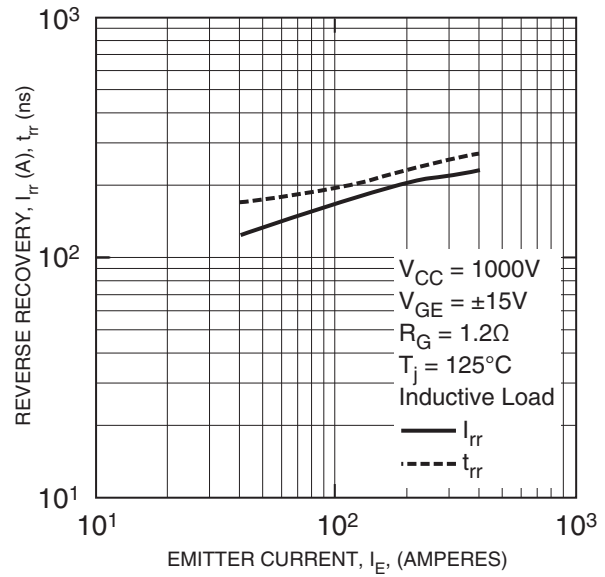


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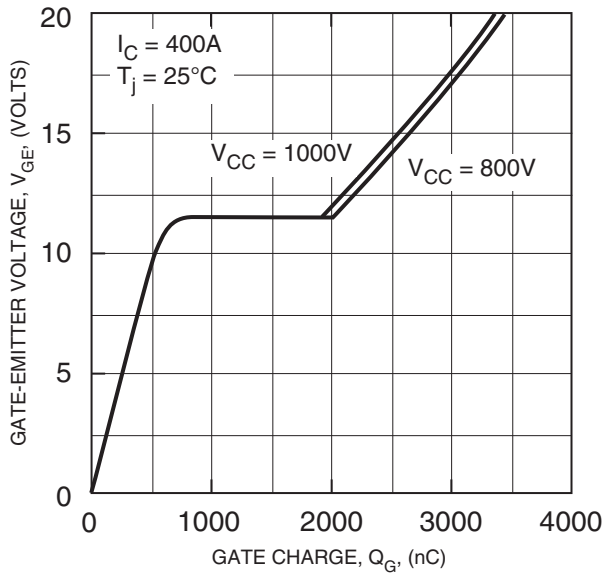
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE VS. V_{GE}



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

